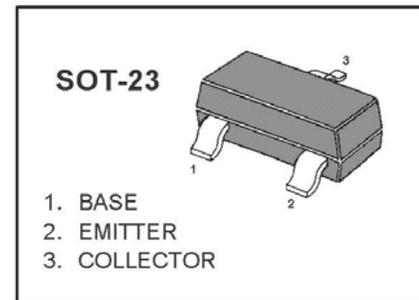


PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, S and Q, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations



MARKING: M6

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	-60	V
Collector Emitter Voltage	V_{CEO}	-50	V
Emitter Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = -10\text{V}$, $I_C = -2\text{mA}$ Current Gain Group	2001 h_{FE}	130	-	240	-
	2001S h_{FE}	240	-	350	-
	2001Q h_{FE}	350	-	450	-
Collector Base Cutoff Current at $V_{CB} = -20\text{V}$	I_{CBO}	-	-	-0.1	μA
Collector Emitter Cutoff Current at $V_{CE} = -10\text{V}$	I_{CEO}	-	-	-100	μA
Collector Base Breakdown Voltage at $I_C = -10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	-60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = -2\text{mA}$	$V_{(BR)CEO}$	-50	-	-	V
Emitter Base Breakdown Voltage at $I_C = -10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	-7	-	-	V
Collector Emitter Saturation Voltage at $I_C = -100\text{ mA}$, $I_B = -10\text{ mA}$	$V_{CE(sat)}$	-	-0.2	-0.5	V
Gain Bandwidth Product at $V_{CE} = -10\text{ V}$, $I_C = -2\text{mA}$	f_T	-	150	-	MHz
Output Capacitance at $V_{CB} = -10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	2	-	pF

MMBT2SC2001

